

Title (en)

A METHOD AND APPARATUS FOR FORMING A HIGH QUALITY LOW TEMPERATURE SILICON NITRIDE LAYER

Title (de)

VERFAHREN UND VORRICHTUNG ZUR HERSTELLUNG EINES HOCHQUALITÄTSFILMES BEI NIEDRIGTEMPERATUR

Title (fr)

PROCEDE ET APPAREIL DE FORMATION D'UNE COUCHE DE NITRURE DE SILICIUM DE HAUTE QUALITE, A FAIBLES TEMPERATURES

Publication

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Application

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Abstract (en)

[origin: WO2004057653A2] A method of forming a silicon nitride layer is described. According to the present invention, a silicon nitride layer is deposited by thermally decomposing a silicon/nitrogen containing source gas or a silicon containing source gas and a nitrogen containing source gas at low deposition temperatures (e.g., less than 550 DEG C) to form a silicon nitride layer. The thermally deposited silicon nitride layer is then treated with hydrogen radicals to form a treated silicon nitride layer.

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